

Description

The IPD40DP06NMATMA1 uses advanced trench technologyto provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = -60V I_D =-10 A

 $R_{DS(ON)}$ < 140m Ω @ V_{GS}=10V

Application

Brushless motor

Load switch

Uninterruptible power supply

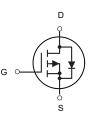
Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
IPD40DP06NMATMA1	TO-252-2L	40DP06NM XXXX	2500	

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units		
Vds	Drain-Source Voltage	-60	V		
Vgs	Gate-Source Voltage	Gate-Source Voltage ±20			
I₀@Tc=25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-10	А		
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	Continuous Drain Current, V _{GS} @ -10V ¹ -8.3			
Ідм	Pulsed Drain Current ²	Pulsed Drain Current ² -26			
EAS	Single Pulse Avalanche Energy ³ 29.8		mJ		
las	Avalanche Current -24.4		А		
P₀@Tc=25°C	Total Power Dissipation ⁴ 31.3		W		
PD@TA=25°C	Total Power Dissipation ⁴ 2		W		
Тятд	Storage Temperature Range -55 to 150		°C		
TJ	Operating Junction Temperature Range -55 to 150		°C		
Reja	Thermal Resistance Junction-Ambient ¹ 62		°C/W		
Rejc	Thermal Resistance Junction-Case ¹	4.0 °C/W			





P-Channel MOSFET



P-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-60			V
$\triangle \text{BV}_{\text{DSS}} / \triangle \text{T}$	BV _{DSS} Temperature Coefficient	Reference to 25° C , I _D =-1mA		-0.049		V/°C
D	Statia Drain Source On Desistance ²	V _{GS} =-10V , I _D =-8A		125	140	
RDS(ON)	$R_{DS(ON)}$ Static Drain-Source On-Resistance ² V_{GS} =-4.5V, I_D =-6A		168	210	mΩ	
$V_{\text{GS(th)}}$	Gate Threshold Voltage		-1.0		-2.5	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_{D}=-250$ uA		5.42		mV/°C
1	Drein Source Lookana Current	V _{DS} =-48V , V _{GS} =0V , T _J =25°C			1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V , V _{GS} =0V , T _J =150°C			5	
I _{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-5A		5.8		S
Qg	Total Gate Charge (-4.5V)			5.85		
Q_{gs}	Gate-Source Charge	V _{DS} =-20V , V _{GS} =-4.5V , I _D =-5A		2.9		nC
Q_gd	Gate-Drain Charge			1.8		
T _{d(on)}	Turn-On Delay Time			10		
Tr	Rise Time	V_{DD} =-12V , V_{GS} =-10V , R_G =3.3 Ω ,		17		ns
T _{d(off)}	Turn-Off Delay Time	I _D =-5A		22		
T _f	Fall Time			21		
C _{iss}	Input Capacitance			715		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , F=1MHz		51		pF
C _{rss}	Reverse Transfer Capacitance			34		
ls	Continuous Source Current ^{1,5}	──V _G =V _D =0V , Force Current			-9.5	А
I _{SM}	Pulsed Source Current ^{2,5}	$v_{G} = v_{D} = 0v$, Force Current			-24	А
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25°C			-1.2	V
t _{rr}	Reverse Recovery Time			10.2		nS
Q _{rr}	Reverse Recovery Charge	I⊧=-8A , dl/dt=100A/μs , Tյ=25°C		5.4		nC

Note :

1. The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2. The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

3. The EAS data shows Max. rating. The test condition is V_{DD} =-25V, V_{GS} =-10V,L=0.1mH,I_{AS}=-15A

4. The power dissipation is limited by 150°C junction temperature

5. The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



IPD40DP06NMATMA1 P-Channel Enhancement Mode MOSFET

Typical Characteristics

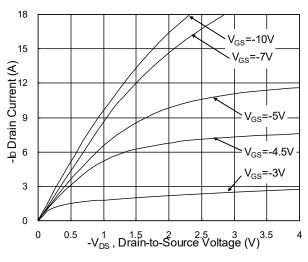


Fig.1 Typical Output Characteristics

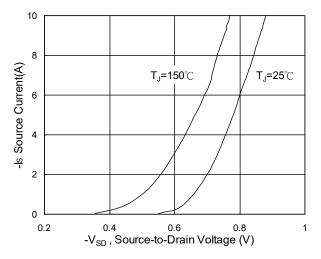


Fig.3 Forward Characteristics Of Reverse

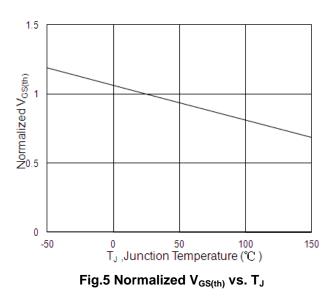


Fig.2 On-Resistance vs. G-S Voltage

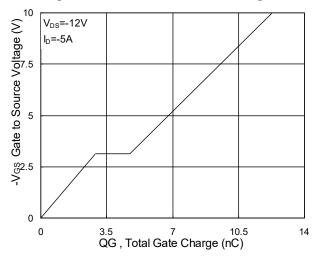


Fig.4 Gate-Charge Characteristics

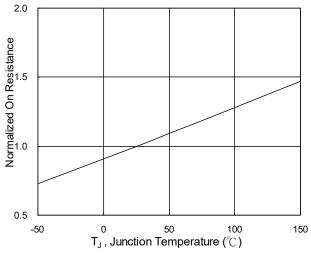
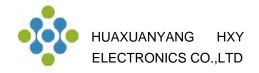


Fig.6 Normalized R_{DSON} vs. T_J



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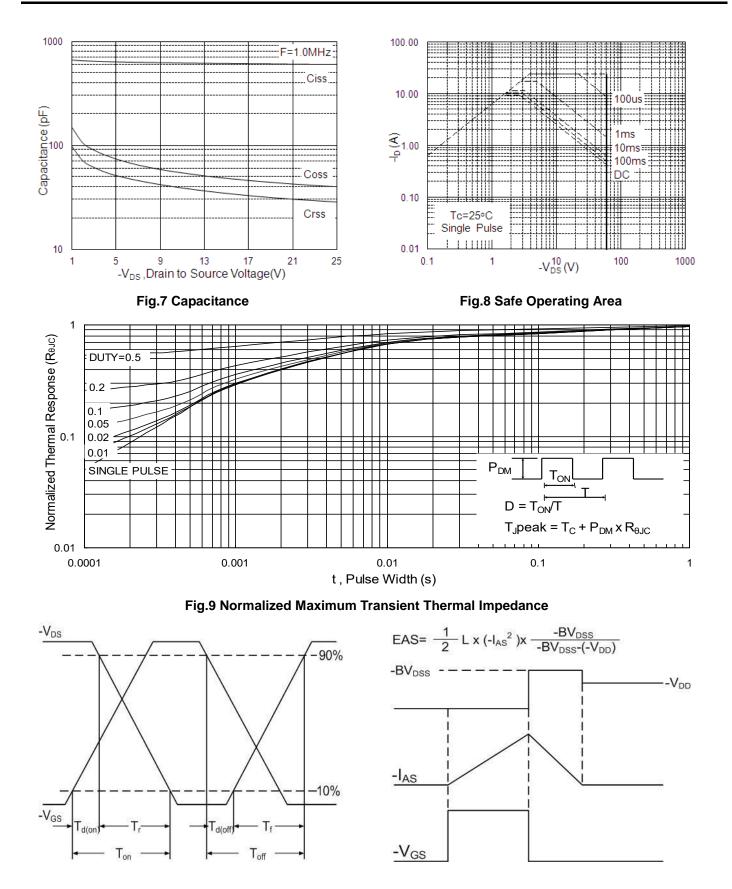
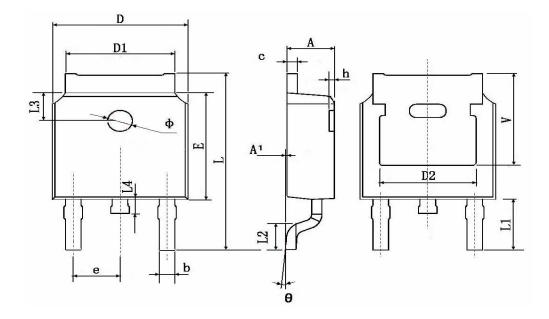


Fig.10 Switching Time Waveform

Fig.11 Unclamped Inductive Switching Waveform



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
с	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190 TYP.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0 °	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP. 0.211 TYP.		TYP.		



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